



Press Contacts:

Eileen Elam
KJ Communications (in the U.S. for ISi)
Tel: +1 408 927-7753
eileen@kjcompr.com

Nick Foot
Billings PR (in Europe for ISi)
Tel: +44 1491 636393
nick.foot@billings-europe.com

Innovative Silicon Names Michael Van Buskirk Senior Vice President of Engineering and Operations

Renowned Flash Memory Veteran to Champion Z-RAM Technology Adoption

SANTA CLARA, Calif. — September 02, 2008 — Innovative Silicon, Inc. (ISi), developer of the Z-RAM® zero-capacitor floating body memory technology, today announced that renowned memory innovator and pioneer Michael Van Buskirk has joined the company as senior vice president of engineering and operations. He is charged with overseeing the continued development of the company's Z-RAM memory technology and deploying it to customer licensees. Van Buskirk directly reports to Mark-Eric Jones, president and CEO of ISi.

“In my many years developing semiconductor memory offerings, I have seldom seen a technology as revolutionary as Z-RAM,” said Michael Van Buskirk. “As DRAM capacitors are becoming nearly impossible to shrink, Z-RAM is well poised to be the DRAM memory of choice for the next generation of IC designs. I am very excited to work with this elegant single-transistor floating body memory technology and the talented global ISi team.”

“Mike has established himself as a major force in the memory industry, and he is the ideal leader as we transition Z-RAM to high-volume manufacturing,” said Mark-Eric Jones. “He has a proven record of migrating advanced-memory technologies from early concept to multi-billion dollar production volumes. I am delighted that Mike will oversee the deployment of Z-RAM to our growing customer base.”

Van Buskirk, a 30-year semiconductor industry veteran, comes to ISi from Spansion (NASDAQ: SPSN) where he was CTO and corporate vice president of engineering. While at Spansion, he spearheaded a number of memory innovations, including Spansion's MirrorBit™ technology, used in a majority of the company's Flash memory products. Spansion was established in 2003 by combining the AMD (NYSE:



AMD) and Fujitsu (TSE: 6707) memory operations. At both AMD and Spansion, Van Buskirk was responsible for the overall memory technology strategy, product design and development, and future product architecture. His other notable achievements include his role as lead inventor of AMD's negative gate erase technology and award winning simultaneous read-write architecture.

Prior to joining AMD in 1986, Van Buskirk was director of engineering non-volatile digital products at PMC-Sierra (NASDAQ: PMCS), formerly Sierra Semiconductor Corp. He began his career at Intel (NASDAQ: INTC) developing EPROM. Van Buskirk has authored a number of technical publications and has been instrumental in securing more than 65 U.S. patents in the field of non-volatile memory over his career. Van Buskirk also serves on the Oregon State University College of Engineering Advisory Board.

About Innovative Silicon

Innovative Silicon, Inc. (ISi) is the inventor and licensor of the Z-RAM® ultra-dense memory technology for stand-alone DRAM and embedded memory applications. Z-RAM is the world's lowest-cost semiconductor memory technology – simpler to manufacture than DRAM, and a fraction the size of SRAM. ISi and the Z-RAM technology have received numerous industry awards, including the World Economic Forum's selection of ISi as a 2008 Technology Pioneer, and IEEE Spectrum Magazine's selection of Z-RAM as the 2007 "Emerging Technology Most Likely to Succeed." Z-RAM is a "Zero Capacitor," true single-transistor floating body memory that eliminates the complex capacitor found in today's DRAM technologies – a fundamental roadblock to Moore's Law of scaling. Z-RAM provides semiconductor manufacturers a solution for nanoscale manufacturing processes that can dramatically lower semiconductor costs. The Z-RAM memory technology has been licensed by Hynix Semiconductor for use in its DRAM chips, and by AMD for use in microprocessors. Since 2003, the company has closed three funding rounds totaling \$47 million, received over 30 patents on the technology, developed test chips in multiple technologies from 90nm to 32nm, and has established global R&D, engineering and support centers in Europe, Asia and North America. For more information see www.z-ram.com.

Z-RAM is a registered trademark of Innovative Silicon, Inc. All other trademarks and registered trademarks are the property of their respective owners.

###

